



40V Dual N-Channel Enhancement Mode MOSFET

Voltage

40 V

Current

37 A

Features

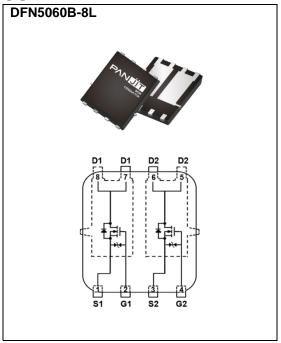
- RDS(ON), VGS@10V, ID@10A<12.3m Ω
- RDS(ON), VGS@4.5V, ID@6A<15.7m Ω
- Excellent FOM
- Logic Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN5060B-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.092 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETE	SYMBOL	LIMIT	UNITS		
Drain-Source Voltage		V _{DS}	40	V	
Gate-Source Voltage		V _{GS}	±20		
Continuous Drain Current ^(Note 3)	T _C =25°C		37		
	T _C =100°C		26	Α	
Pulsed Drain Current(Note 1)	T _C =25°C	I _{DM}	148		
Power Dissipation	T _C =25°C	D-	30	147	
	T _C =100°C	Po	15	W	
Continuous Drain Current(Note 4)	T _A =25°C		10.6	Δ.	
	T _A =70°C	l _D	9	A	
Power Dissipation	T _A =25°C	D-	2.5	W	
	T _A =70°C	PD	1.8		
Single Pulse Avalanche Energy ^(Note 5)		Eas	42	mJ	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~175	°C	
Thermal Resistance ^(Note 4)	Junction to Case	R _{0JC}	5	°C/W	
	Junction to Ambient	$R_{\theta JA}$	60		





Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	40	-	-	V		
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =50uA	1.1	1.6	2.3			
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =10A	-	9.8	12.3	mΩ		
		V _{GS} =4.5V, I _D =6A	-	12.1	15.7			
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	uA		
Gate-Source Leakage Current		V _{GS} =±20V, V _{DS} =0V	-	-	±10	uA		
	I _{GSS}	V _{GS} =±10V, V _{DS} =0V	-	-	±1			
Dynamic ^(Note 6)								
Total Gate Charge	Qg	V _{DS} =32V, I _D =10A, V _{GS} =10V	-	13	-	nC		
Gate-Source Charge	Qgs		-	3	-			
Gate-Drain Charge	Q_{gd}		-	2	-			
Input Capacitance	Ciss	V _{DS} =25V, V _{GS} =0V, f=1MHz	-	778	-	pF		
Output Capacitance	Coss		-	180	-			
Reverse Transfer Capacitance	Crss		-	25	-			
Gate resistance	Rg	f=1MHz	-	1.6	-	Ω		
Turn-On Delay Time	td _(on)	V_{DS} =32V, I_{D} =10A, V_{GS} =10V, R_{G} =3 Ω (Note 2)	-	7	-	ns		
Turn-On Rise Time	tr		-	78	-			
Turn-Off Delay Time	td(off)		-	26	-			
Turn-Off Fall Time	tf		-	56	-			
Drain-Source Diode			_					
Diode Forward Current	Is	Tc=25°C	-	-	37	Α		
Pulsed Diode Forward Current	I _{SM}	TC=25 C	-	-	148			
Diode Forward Voltage	V _{SD}	I _S =20A, V _{GS} =0V	-	0.9	1.3	V		
Reverse Recovery Time	Trr	V _{GS} =0V, I _S =20A	-	20	-	ns		
Reverse Recovery Charge	Qrr	dl _S /dt=100A/us	-	10	-	nC		

NOTES:

- 1. Pulse width<a>100us, Duty cycle<a>2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Chip capability with an R_{0JC}=5°C/W.
- 4. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 5. The test condition is L=0.5mH, I_{AS} =13A, V_{DD} =30V, V_{GS} =10V, Starting T_{J} =25°C.
- 6. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

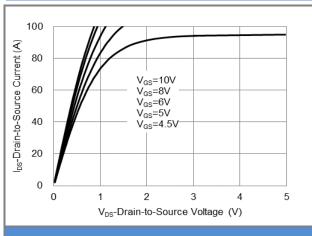


Fig.1 On-Region Characteristics

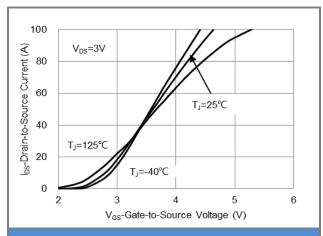


Fig.2 Transfer Characteristics

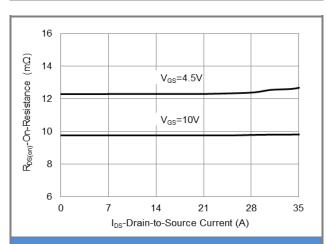


Fig.3 On-Resistance vs. Drain Current

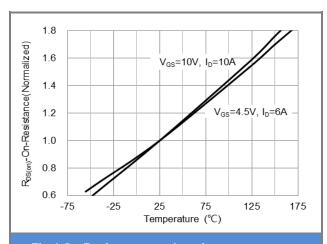
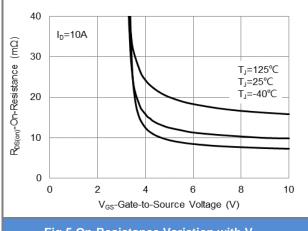


Fig.4 On-Resistance vs. Junction temperature





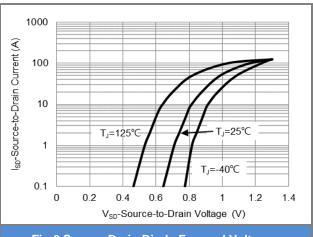


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

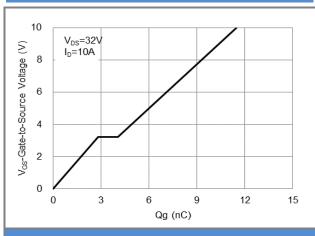


Fig.7 Gate-Charge Characteristics

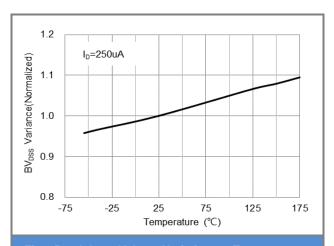


Fig.8 Breakdown Voltage Variation vs. Temperature

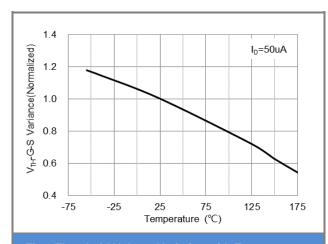


Fig.9 Threshold Voltage Variation with Temperature

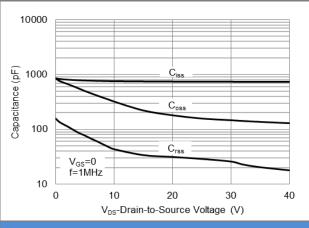


Fig.10 Capacitance vs. Drain-Source Voltage

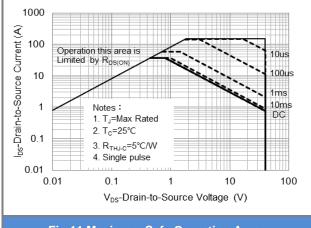


Fig.11 Maximum Safe Operating Area

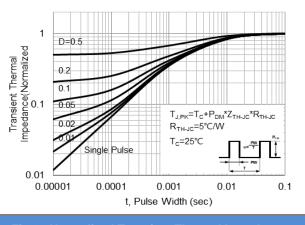


Fig.12 Normalized Transient Thermal Impedance

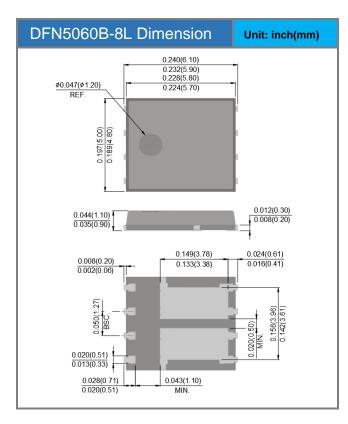


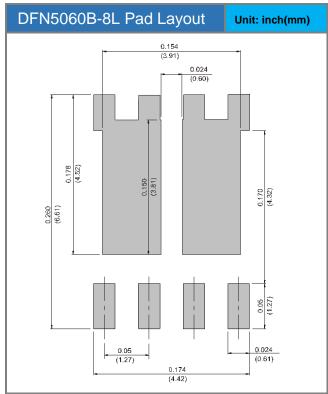


Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ5948-AU_R2_002A1	DFN5060B-8L	3K pcs / 13" reel	Q5948	Halogen free RoHS compliant

Packaging Information & Mounting Pad Layout









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